

# **isc Silicon NPN Darlington Power Transistor**

2SD1524

#### **DESCRIPTION**

- · Collector-Emitter Breakdown Voltage-
- : V<sub>(BR)CEO</sub>= 450V(Min)
- · High DC Current Gain
  - : h<sub>FE</sub>= 300(Min) @ I<sub>C</sub>= 5A, V<sub>CE</sub>= 3V
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

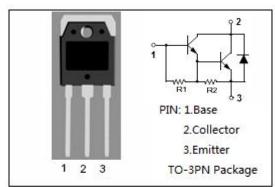


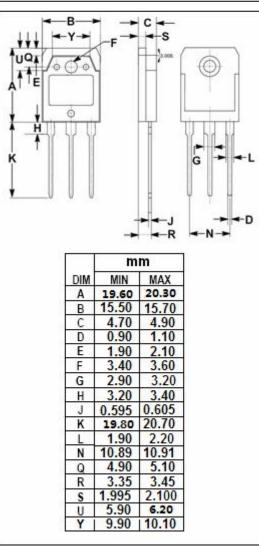
### **APPLICATIONS**

 Designed for audio frequency power amplifier and low speed high current switching industrial applications.

## ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	450	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	450	V	
V <sub>EBO</sub>	Emitter-Base Voltage	7	V	
Ic	Collector Current-Continuous	10	А	
I <sub>CM</sub>	Collector Current-Peak	20	А	
Pc	Collector Power Dissipation @T <sub>a</sub> =25°C	3	- W	
	Collector Power Dissipation @Tc=25°C	100		
Tj	Junction Temperature	150	$^{\circ}$ C	
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$ C	







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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

T <sub>C</sub> =25°C unless otherwise specified									
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT			
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 30mA, I <sub>B</sub> = 0	450			V			
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 20mA ,I <sub>C</sub> = 0	7			V			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A, I <sub>B</sub> = 8mA			1.5	V			
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = 5A, I <sub>B</sub> = 8mA			2.0	V			
І <sub>СВО</sub>	Collector Cutoff current	V <sub>CB</sub> = 500V, I <sub>E</sub> = 0			0.1	mA			
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7V; I <sub>C</sub> = 0			20	mA			
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 5A; V <sub>CE</sub> = 3V	300						
Switching Times									
ton	Turn-On Time			1.5		μ <b>S</b>			
tstg	Storage Time	$I_{C} = 5A, I_{B1} = I_{B2} = 8mA$		7.0		μ \$			
t <sub>f</sub>	Fall Time			4.0		μ \$			

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